Highly confined low-loss plasmons in graphene-boron nitride heterostructures

¹ICFO – The Insititute of Photonic Sciences, 08860 Castelldefels (Barcelona), Spain 2 Dep. of Mechanical Engineering, Columbia University, New York, NY 10027, USA 3 Dep. of Physics and Astronomy, University of Missouri, Columbia, Missouri 65211, USA 4 CIC nanoGUNE Consolider, 20018 Donostia-San Sebastián, Spain ⁵NEST, Istituto Nanoscienze - CNR and Scuola Normale Superiore, 56126 Pisa, Italy 6 SPIN-CNR, Via Dodecaneso 33, 16146 Genova, Italy $⁷$ National Institute for Materials Science, 1-1 Namiki, Tsukuba 305-0044, Japan</sup> 8 IKERBASQUE, Basque Foundation for Science, 48011 Bilbao, Spain

Graphene plasmonics is an excellent platform for strong optical field confinement with relatively low damping. This enables new device classes for deep subwavelength metamaterials [1,2], single-photon nonlinearities [3], extraordinarily strong lightmatter interactions [4] and nano-optoelectronic switches.

The problem was that thus far strong plasmon damping was observed [5-7], with both impurity scattering [8] and many-body effects in graphene [5] proposed as possible explanations. This strong damping hindered the further development of graphene plasmonic devices.

Using van der Waals heterostructures [9] new methods to integrate graphene with other atomically flat materials have become available. Especially graphene encapsulated between two films of hexagonal boron nitride (h-BN) shows extremely high room temperature transport mobility of charge carriers which is only limited by the scattering with acoustic phonons in the graphene [10].

We show results were we exploit near-field microscopy to image propagating plasmons in high quality graphene encapsulated between h-BN [11]. Frequency dispersion and particularly plasmon damping in real space is determined and we show that these high quality graphene samples show unprecedented low plasmon damping combined with extremely strong field confinement. We identify that the main damping channels are intrinsic thermal phonons in the graphene [12] as well as dielectric losses in the h-BN [13]. These results are the key for the development of graphene nano-photonic and nano-optoelectronic devices.

References

- [1] Z. Fang et al., Nano Lett. 14, 299 (2014).
- [2] A. N. Grigorenko, M. Polini, and K. S. Novoselov, Nature Photon. 6, 749 (2012).
- [3] M. Gullans et al., Phys. Rev. Lett. 111, 247401 (2013).
- [4] .H.L. Koppens, D.E. Chang, and F.J. García de Abajo, Nano Lett. 11, 3370 (2011).
- [5] Z. Fei et al., Nature 487, 82 (2012).
- [6] J. Chen et al., Nature 487, 77 (2012).
- [7] P. Alonso-González et al., Science 344, 1369 (2014).
- [8] A. Principi, G. Vignale, M. Carrega, and M. Polini, Phys. Rev. B 88, 121405(R) (2013).
- [9] A. K. Geim and I. V. Grigorieva, Nature 499, 419 (2013).
- [10] L. Wang et al., Science 342, 614 (2013).
- [11] A. Woessner, M.B. Lundeberg, Y. Gao et al., arXiv:1409.5674 (2014).
- [12] A. Principi et al., arXiv:1408.1653 (2014).
- [13] J. D. Caldwell et al., arXiv:1404.0494 (2014).

Oral PhD

Achim Woessner¹ ,

M. B. Lundeberg¹, Y. Gao², A. Principi³, P. Alonso-González⁴, M. Carrega^{5,6}, K. Watanabe⁷, T. Taniguchi⁷, G. Vignale³, M. Polini⁵, J. Hone², R. Hillenbrand^{4,8} and F. H.L. Koppens $¹$ </sup>

achim.woessner@icfo.es frank.koppens@icfo.es